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## Sommario/riassunto

Guide to State-of-the-Art Electron Devices is written by 70 world-class specialists who share their expert views on a particular group of electron devices or device aspects. The book's release coincides with the 60th anniversary of the former Institute of Radio Engineers (IRE) electron devices committee and the 35th anniversary of IEEE Electron Devices Society (EDS). Seminal achievements in the field of electron devices are displayed in a history timeline that runs throughout the book. Key features . Organized in a matrix of electron device types and cross-disciplines from photovoltaics and semiconductor manufacturing to VLSI technology and circuits. A timely desk reference with fully-integrated colour and a unique lay-out with sidebars to highlight the key terms. Contributed by IEEE Electron Devices Society (EDS) members from industry, academic and government institutions. Discusses the historical developments and speculates on future trends to give a more

rounded picture of the topics coveredAn essential reference for both present and prospective EDS members, this guide surveys the commonalities and interrelationships of all electron device types covered by the EDS. It will also appeal to affiliate IEEE members wishing to develop their expertise in electron devices.

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